

L Number	Hits	Search Text	DB	Time stamp
1	2342	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/15 13:32
2	2960429	metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/15 13:32
3	1640	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/15 13:33
4	231313	protrusions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/15 13:34
5	49	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and metal and protrusions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/15 13:42
6	2	("6190949") or ("6096581")).PN.	USPAT; US-PGPUB	2003/08/15 13:42
-	0	(heat adj absorb\$3) with insulat\$3 with ((non-single or poly or polycrystalline) adj (film or layer)) with recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:43
-	2	(heat adj absorb\$3) and insulat\$3 and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:47
-	6766	(heat adj absorb\$3) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:01
-	2	((heat adj absorb\$3) and insulat\$3) and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:48
-	0	((heat adj absorb\$3) with metal) and insulat\$3 and amorphous and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:04
-	0	((heat adj absorb\$3) with metal) and insulat\$3 and ((amorphous or non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:05
-	1320	(heat adj absorb\$3) with metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:15
-	499	((heat adj absorb\$3) with metal) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:06

4	((heat adj absorb\$3) with metal) and insulat\$3) and (non-single or poly or polycrystalline) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:08
24	((heat adj absorb\$3) with metal) and insulat\$3) and (non-single or poly or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:08
1888852	((heat adj absorb\$3 or metal) adj layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:08
13	(heat adj absorb\$3 with metal) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:19
538	(heat adj absorb\$3) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:39
1	((heat adj absorb\$3) adj (layer or film) same metal) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:21
0	((heat adj absorb\$3) adj (layer or film) same metal) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:21
105	((heat adj absorb\$3) adj (layer or film) same metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:22
1	((heat adj absorb\$3) adj (layer or film) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:39
20154	((heat adj absorb\$3 or metal) adj layer or film) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:18
3477	((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:19
2873	((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:20
0	((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and irradiat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:21
1208	((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:22

-	628	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:22
-	615	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:23
-	35	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1) and semiconductor) and protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:12
-	0	irradat\$4 with protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:14
-	400	irradiat\$4 with protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:23
-	1	(irradiat\$4 with protrusion\$1) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:16
-	0	((irradiat\$4 with protrusion\$1) with tft) with crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:17
-	0	((irradiat\$4 with protrusion\$1) with tft) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:17
-	24	irradiat\$4 with (protrusion\$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:23
-	220	irradiat\$4 and (protrusion\$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:24
-	0	metal with insulat\$3 with amorphous with irradat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:06
-	21	metal and insulat\$3 and amorphous and irradat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:07
-	121266	metal adj(layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:08
-	121266	metal adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:09

3067	((metal adj (layer or film)) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
2727	((metal adj (layer or film)) and tft) and insulat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
613	((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:11
368	((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
53	((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj island)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
53	((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj island)) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:14
0	tft with island\$1 with amorphous with crystalliz\$5 with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
0	tft and island\$1 with amorphous near5 crystalliz\$5 with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
0	tft and island\$1 and amorphous near5 crystalliz\$5 with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
1	tft with island\$1 with amorphous near5 crystalliz\$5 with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
0	20010045558.URPN.	USPAT	2002/08/15 15:29
0	20010045558.URPN.	USPAT	2002/08/15 15:29
2	protrusion\$1 with crystalliz\$5 adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:08
1	(rough\$4 with recrystalliz\$5) with hsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:09
0	20020036312.URPN.	USPAT	2002/08/15 19:10
711	rough\$4 same recrystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:12

292	rough\$4 with recrystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/15 19:46
8	(rough\$4 with recrystalliz\$5) with amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/15 19:14
0	20020034845.URPN.	USPAT	2002/08/15 19:18
15	("4411734" "4737474" "5089432" "5121186" "5147820" "5147826" "5298436" "5326722" "5418398" "5441904" "5514621" "5604157" "5614428" "5652156" "5712181").PN.	USPAT	2002/08/15 19:23
2	6017819.URPN.	USPAT	2002/08/15 19:39
0	20020036312.URPN.	USPAT	2002/08/15 19:45
5	(rough\$4 with recrystalliz\$5) with semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/15 19:47
1885	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB	2003/08/15 13:31
99764	irradiate or irradiation	USPAT; US-PGPUB	2003/04/06 17:45
595	((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation))	USPAT; US-PGPUB	2003/04/06 17:46
1217179	metal	USPAT; US-PGPUB	2003/04/06 17:46
497	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal	USPAT; US-PGPUB	2003/04/06 17:46
622038	channel	USPAT; US-PGPUB	2003/04/06 17:46
458	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel	USPAT; US-PGPUB	2003/04/06 17:48
325606	semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
451	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
661709	protrusion or project or projection	USPAT; US-PGPUB	2003/04/06 17:50
141	((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor) and (protrusion or project or projection)	USPAT; US-PGPUB	2003/04/06 17:50
4	("5581092" "5959313" "6281057" "6323071").PN.	USPAT	2003/04/06 19:12
0	6506669.URPN.	USPAT	2003/04/06 19:13
0	6506669.URPN.	USPAT	2003/04/06 19:13